



QPC1005

0.15 – 2.8 GHz 50 W GaN SPDT Switch

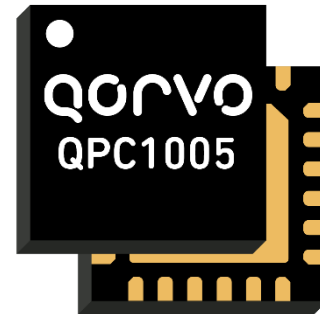
Product Overview

Qorvo's QPC1005 is a Single-Pole, Double-Throw (SPDT) switch fabricated on Qorvo's QGaN25 0.25um GaN on SiC production process.

Operating from 0.15 to 2.8 GHz, the QPC1005 typically supports 50 W input power handling at control voltages of 0/-40 V for both CW and pulsed RF operations. This switch maintains low insertion loss less than 0.7 dB and greater than 30 dB isolation, making it ideal for high power switching applications across both defense and commercial platforms.

QPC1005 is offered in a 4 x 4 mm plastic overmolded QFN package.

Lead-free and RoHS compliant



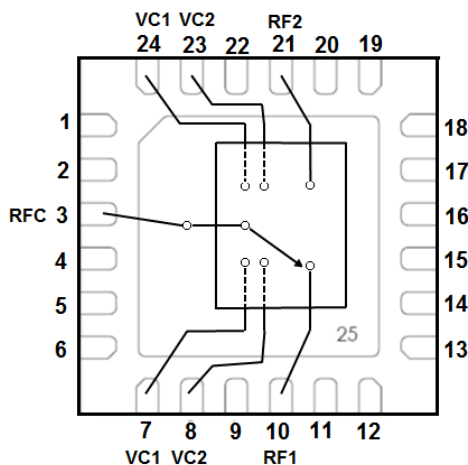
4mm x 4mm 24 Lead OVM QFN

Key Features

- SPDT
- Frequency Range: 0.15 to 2.8 GHz
- Input Power: 50 W
- Insertion Loss: < 0.7 dB
- Isolation: >30 dB Typical
- Switching Speed: 30 ns
- Control Voltages: 0 V/-40 V
- Redundant Control Lines
- Package Dimensions: 4 x 4 x 0.85 mm

Performance is typical across frequency. Please reference electrical specification table and data plots for more details.

Functional Block Diagram



Applications

- Commercial and Military Radar
- Land Mobile Radios
- Military Communications Radios
- Electronic Warfare
- Test Instrumentation
- General Purpose

Ordering Information

Part No.	Description
QPC1005	0.5–2.8 GHz 50 W SPDT Switch
QPC1005PCB4B01	QPC1005 Evaluation Board

Absolute Maximum Ratings

Parameter	Rating
Control Voltage (V_c)	-50 V
Control Current (I_c)	-1.5 / +1.5 mA
Power Dissipation	12 W
RF Input Power, CW, 50 Ω , T = 25 °C	60 W
Mounting Temperature (30 sec)	260 °C
Storage Temperature	-40 to 150 °C

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability.

Recommended Operating Conditions

Parameter	Min	Typ.	Max	Units
V_{C1}		0/-40		V
V_{C2}		-40/0		V
Temperature Range	-40	+25	+85	°C

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

Thermal and Reliability Information

Parameter	Test Conditions	Value	Units
Thermal Resistance (θ_{JC}) ^(1,2)	$T_{BASE} = 85$ °C, $V_{C1} = 0$ V, $V_{C2} = -40$ V, Freq. = 2.8 GHz $P_{IN} = 60$ W, P_{DISS} ⁽³⁾ = 6.5 W, CW	5.23	°C/W
Channel Temperature (T_{CH}) ^(1,2)		119	°C

Notes:

1. Measured to the back of the package.
2. Refer to the following document: [GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)
3. This is a total P_{DISS} in the FETs.

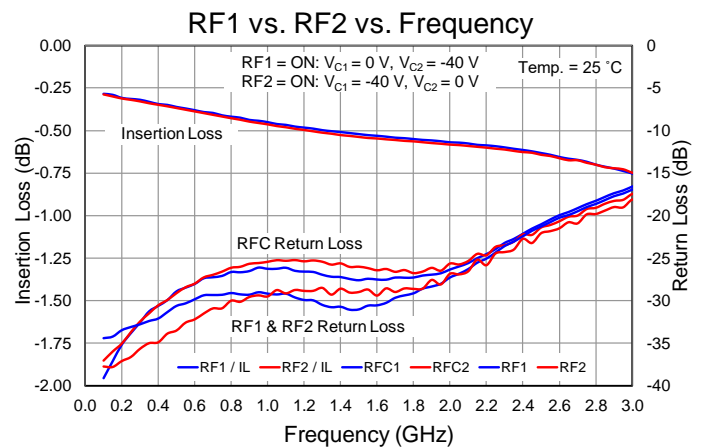
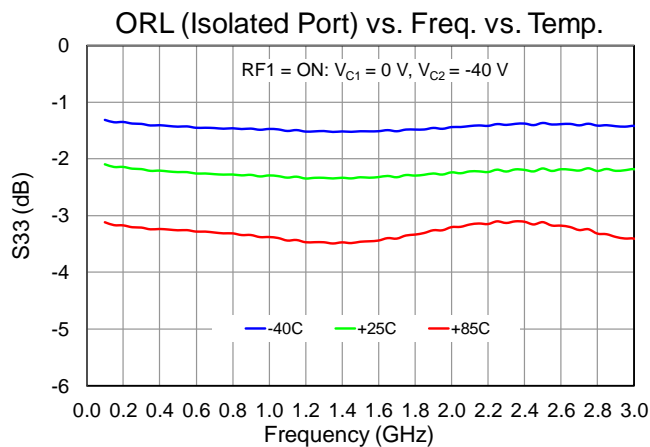
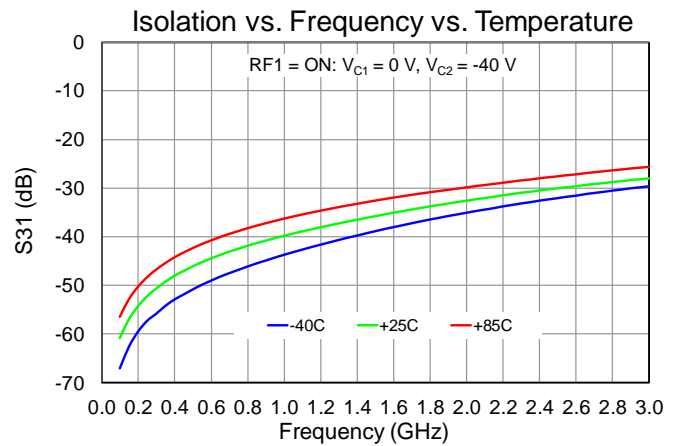
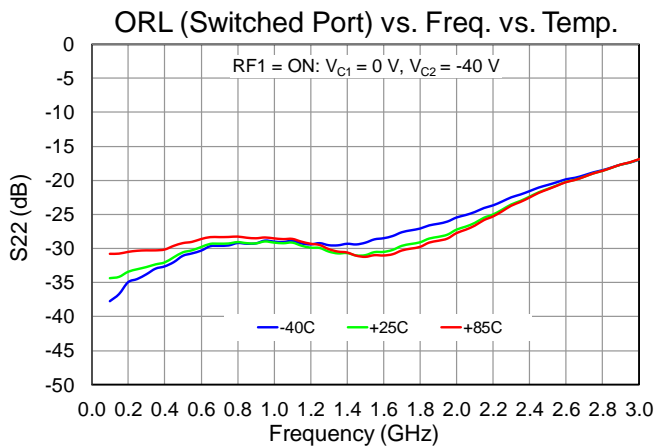
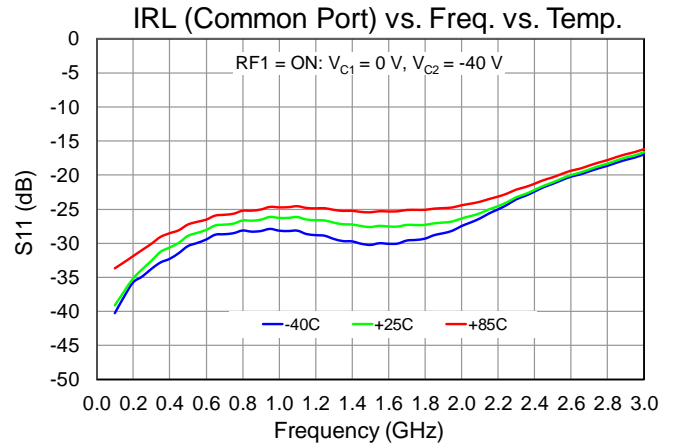
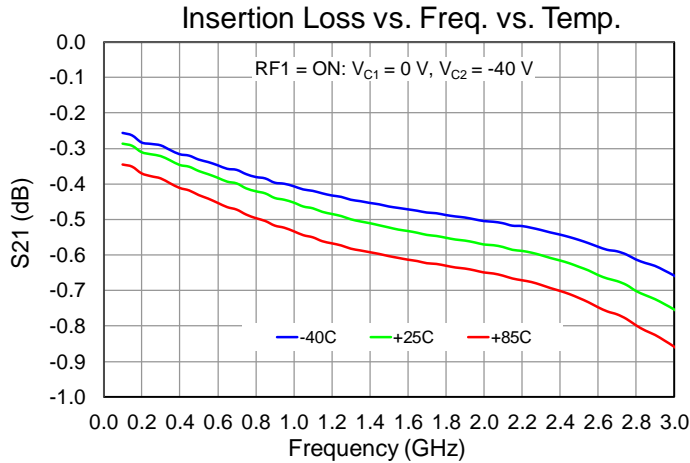
Electrical Specifications

Test conditions unless otherwise noted: 25 °C, $V_{C1} = 0\text{ V}/-40\text{ V}$, $V_{C2} = -40\text{ V}/0\text{ V}$, see function table on page 11.

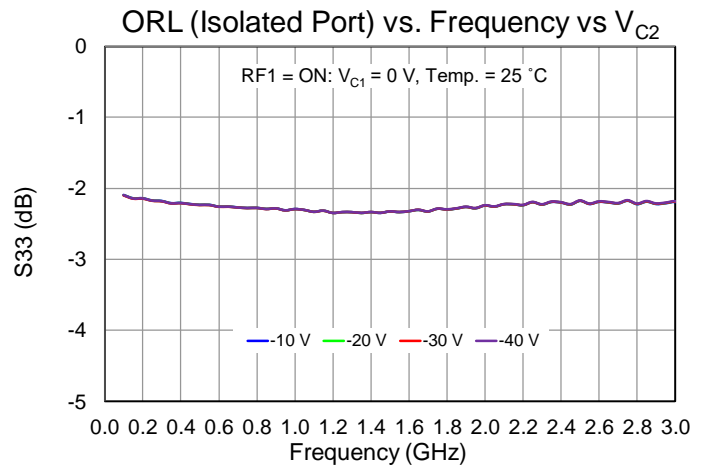
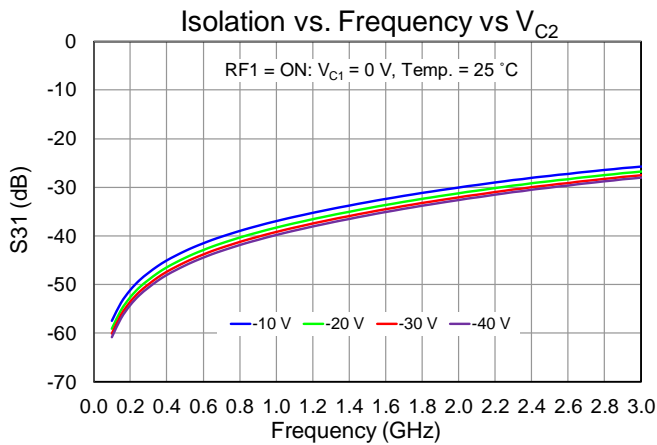
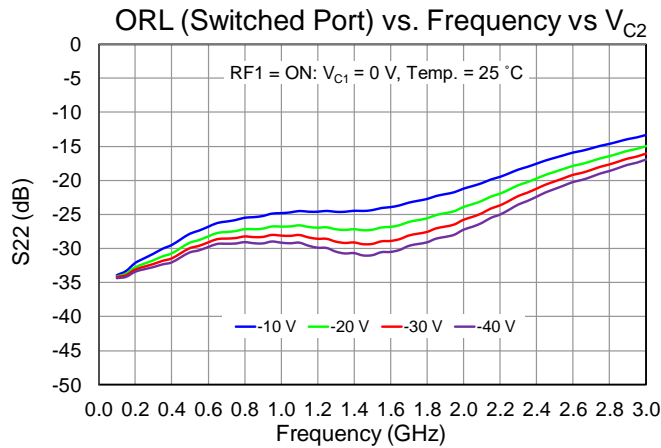
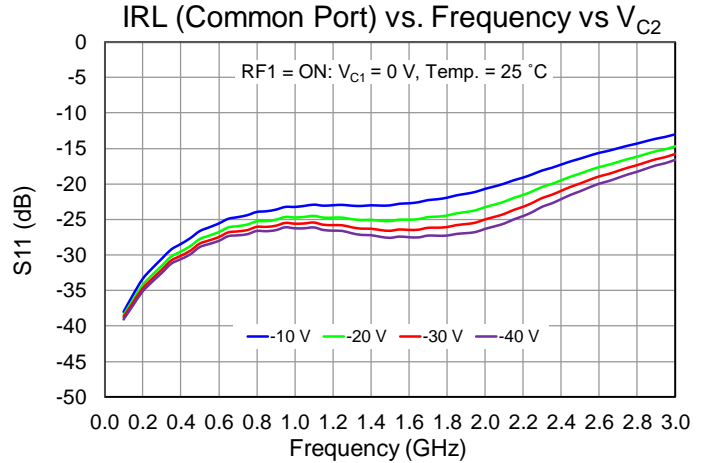
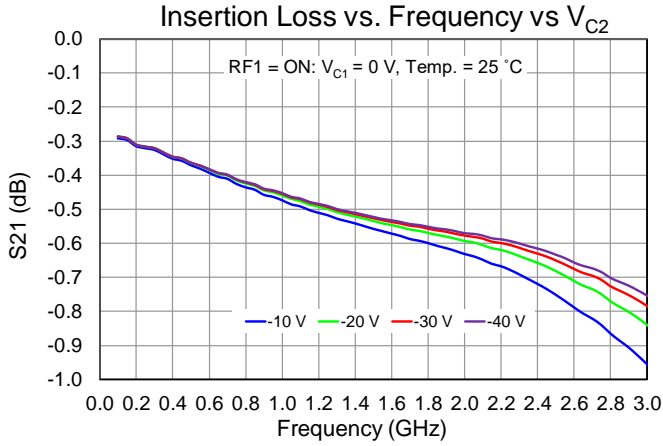
Parameter	Min	Typ.	Max	Units
Operational Frequency Range	0.15	–	2.8	GHz
Insertion Loss (On-State)	Frequency = 0.15 GHz	–	0.30	dB
	Frequency = 1.0 GHz	–	0.45	
	Frequency = 2.8 GHz	–	0.70	
Input Return Loss (On-State) Common Port RL	Frequency = 0.15 GHz	–	37	dB
	Frequency = 1.0 GHz	–	26	
	Frequency = 2.8 GHz	–	18	
Output Return Loss (On-State) Switched Port RL	Frequency = 0.15 GHz	–	34	dB
	Frequency = 1.0 GHz	–	29	
	Frequency = 2.8 GHz	–	18	
Isolation (Off-State)	Frequency = 0.15 GHz	–	57	dB
	Frequency = 1.0 GHz	–	40	
	Frequency = 2.8 GHz	–	29	
Output Return Loss Isolated Port	Frequency = 0.15 GHz	–	2.1	dB
	Frequency = 1.0 GHz	–	2.3	
	Frequency = 2.8 GHz	–	2.2	
Insertion Loss @ $P_{IN} = 47\text{ dBm}$ (Pulsed RF) $PW = 100\mu\text{s}$; $DC = 10\%$	Frequency = 0.15 GHz	–	0.30	dB
	Frequency = 1.0 GHz	–	0.50	
	Frequency = 2.8 GHz	–	0.70	
Insertion Loss @ $P_{IN} = 47\text{ dBm}$ (CW)	Frequency = 0.15 GHz	–	0.30	dB
	Frequency = 1.0 GHz	–	0.50	
	Frequency = 2.8 GHz	–	0.75	
Input Power ($P_{0.1dB}$)	–	47	–	dBm
Control Voltage		-40	-50	V
Total Supply Current		<3		mA
Switching Speed		30		ns
Insertion Loss Temperature Coefficient	–	-0.0015	–	dB/°C

Performance Plots – Small Signal

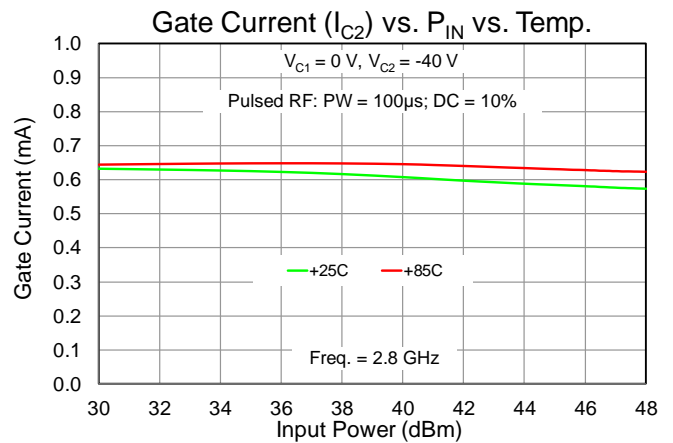
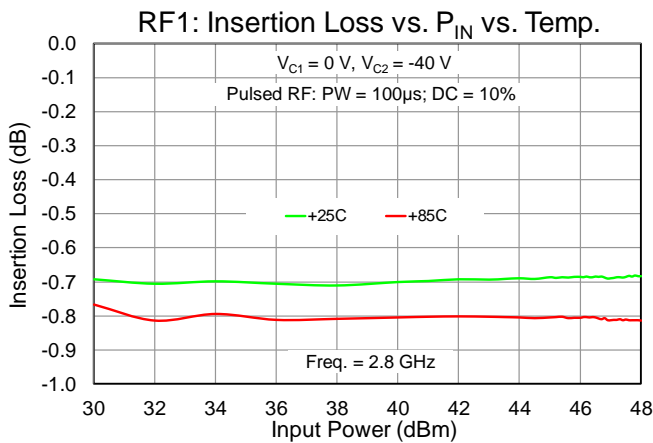
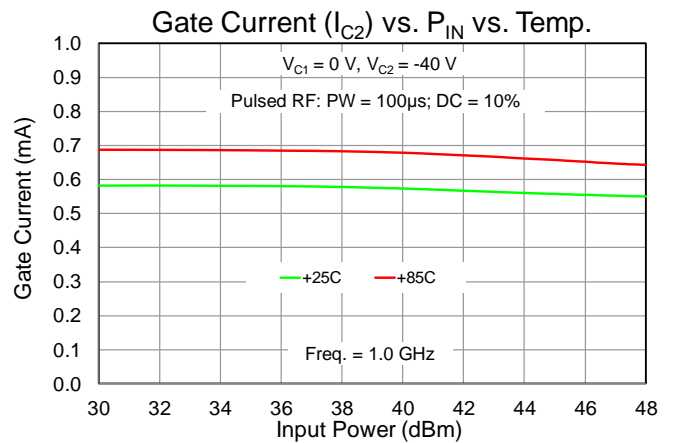
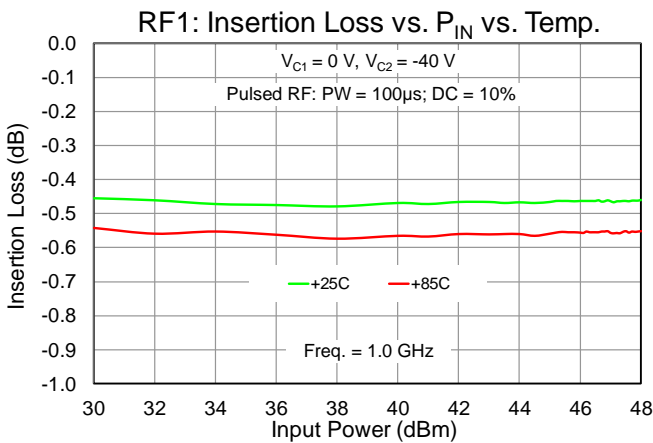
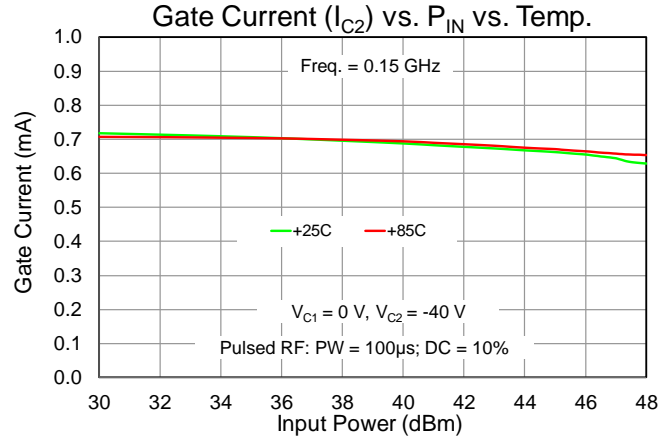
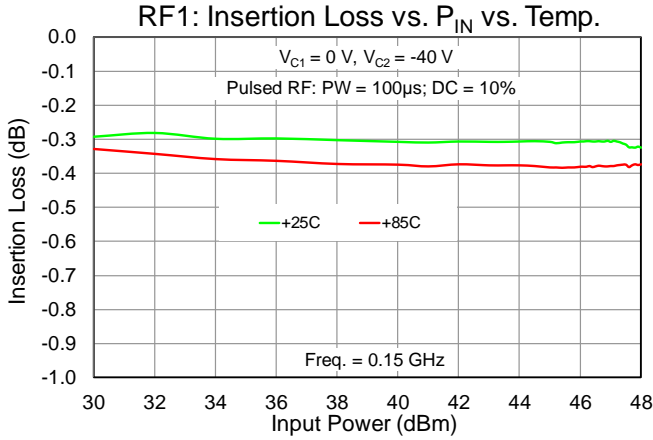
Notes: RFC = Port1; RF1 = Port 2; RF2 = Port 3



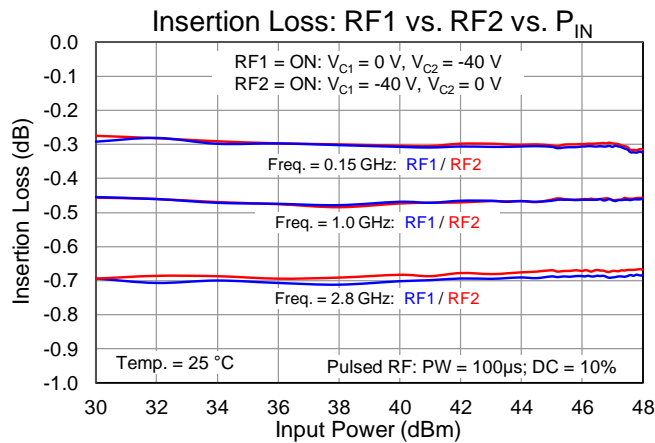
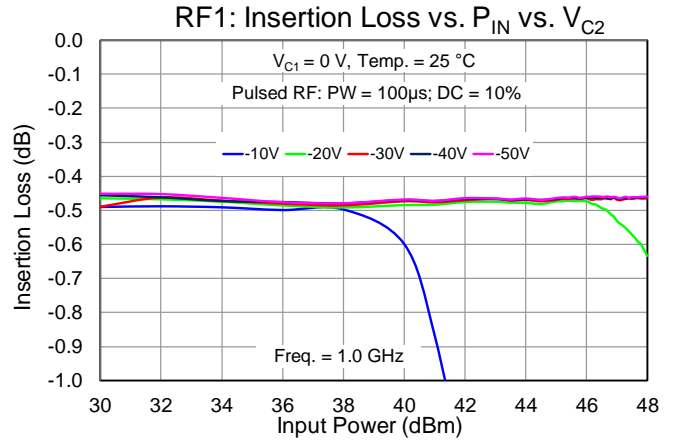
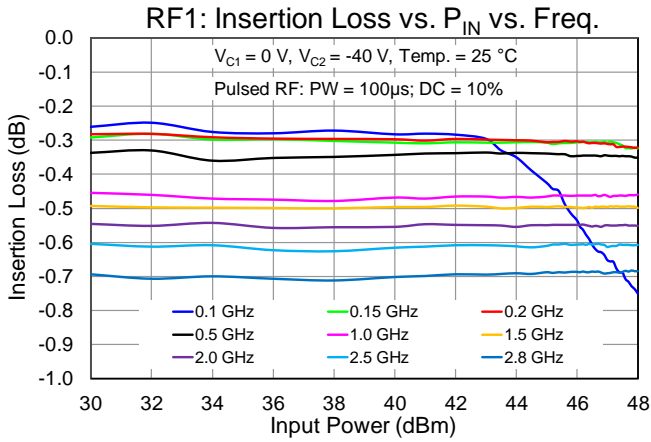
Performance Plots – Small Signal



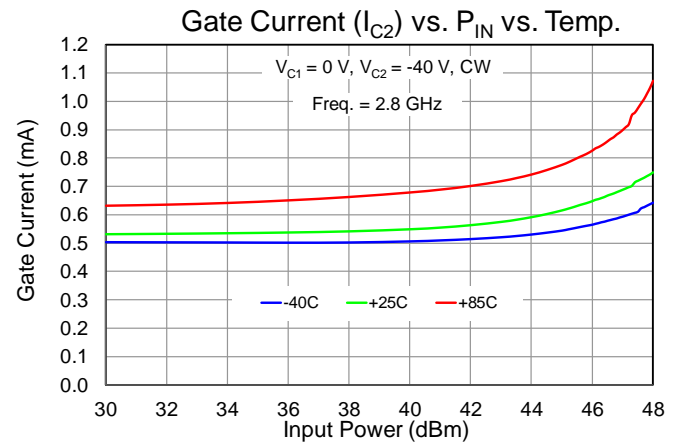
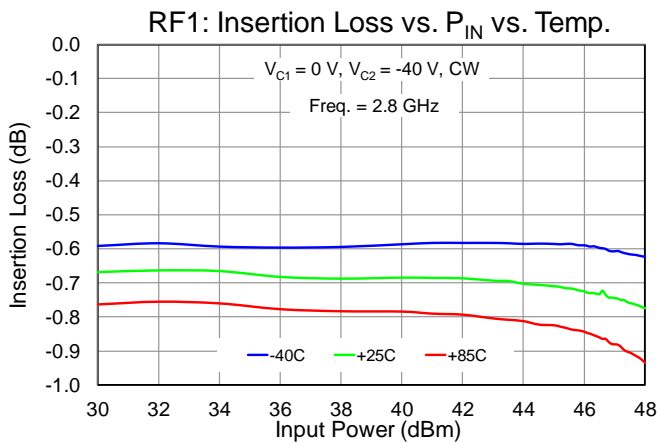
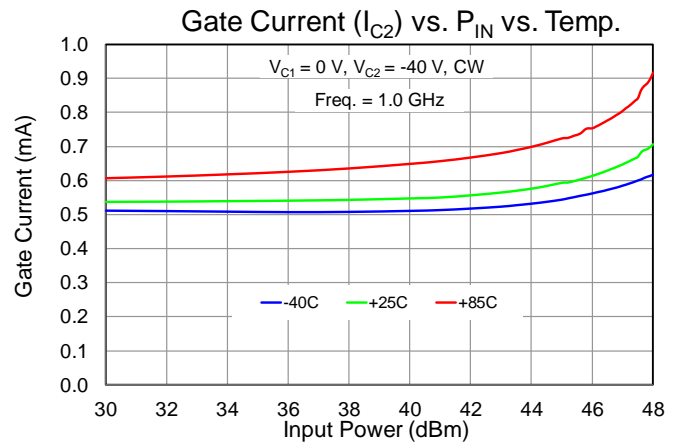
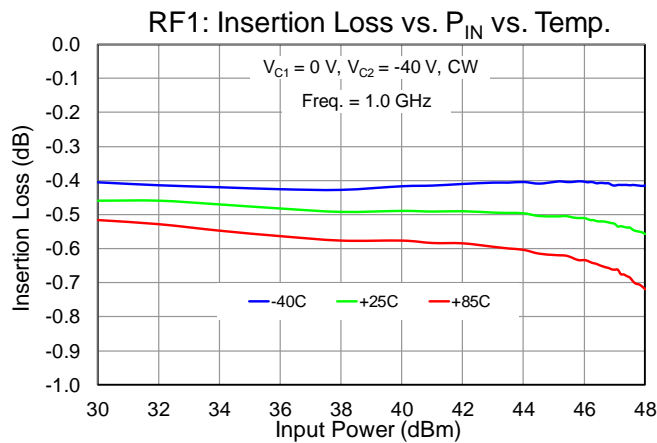
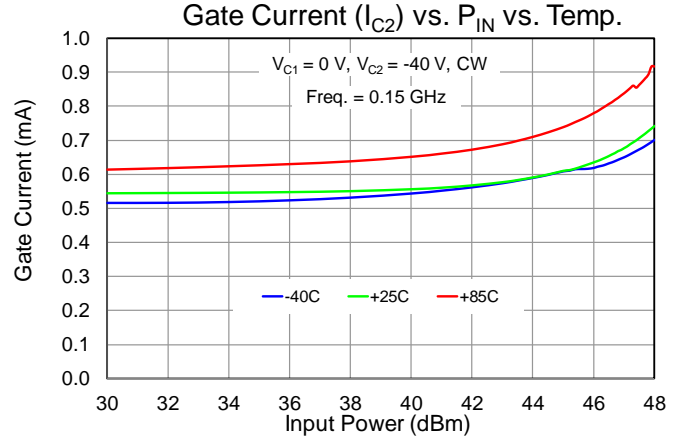
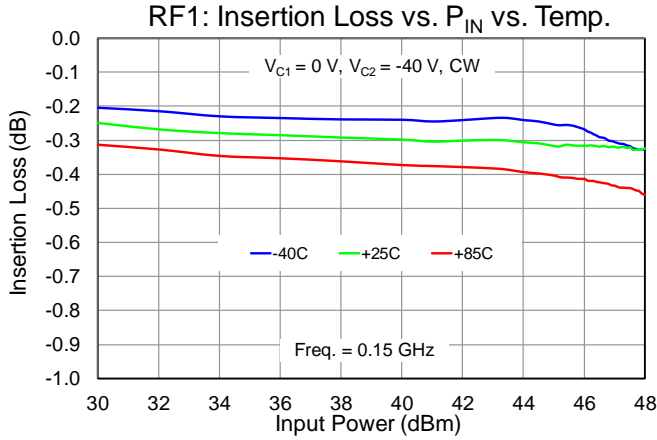
Performance Plots – Compression (Pulsed)



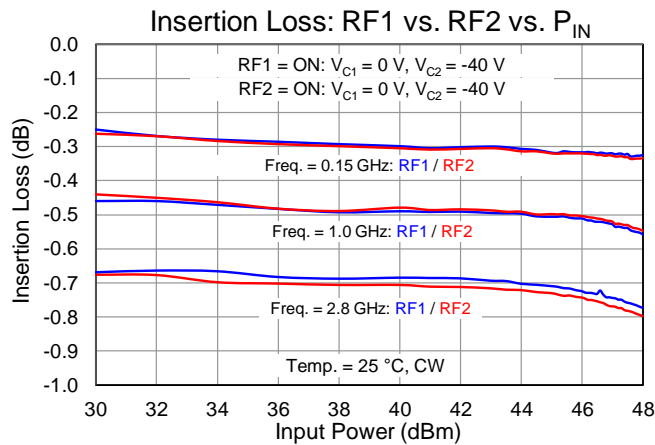
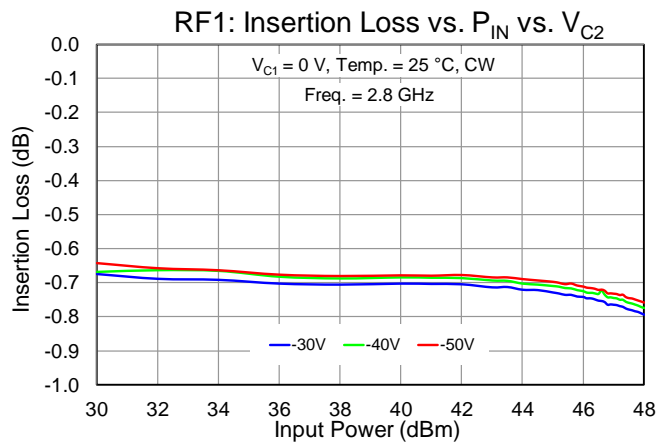
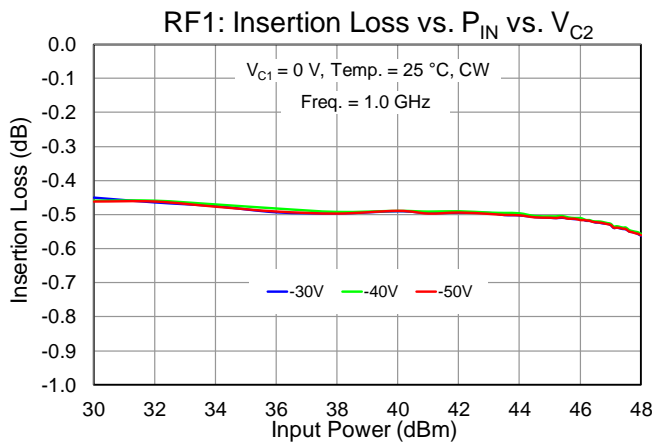
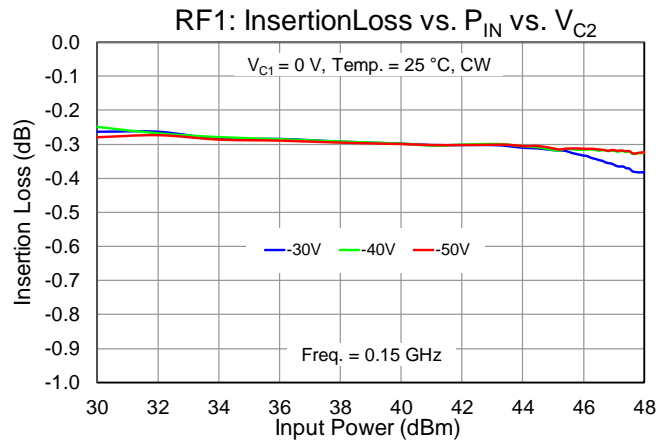
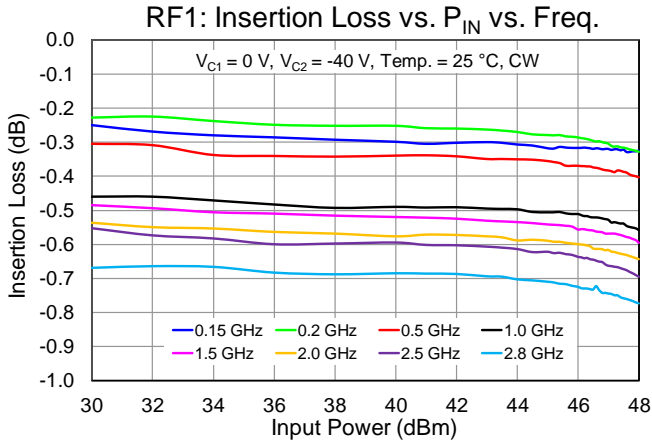
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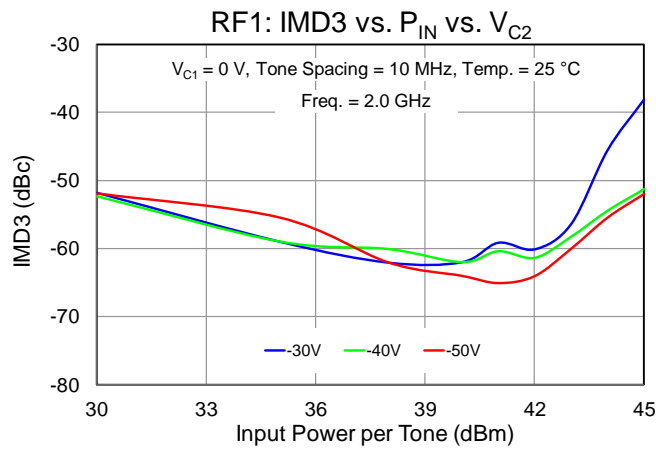
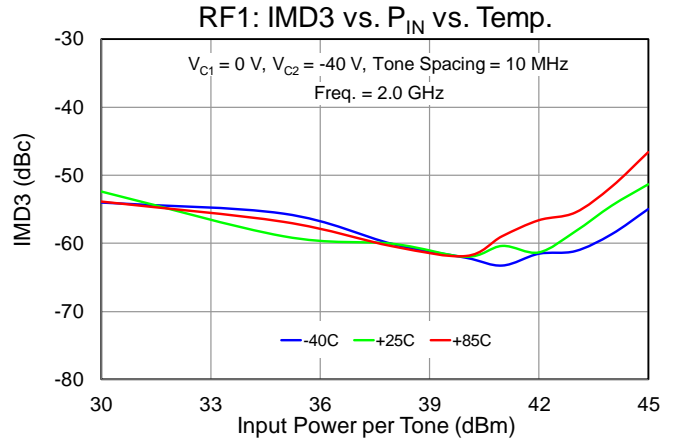
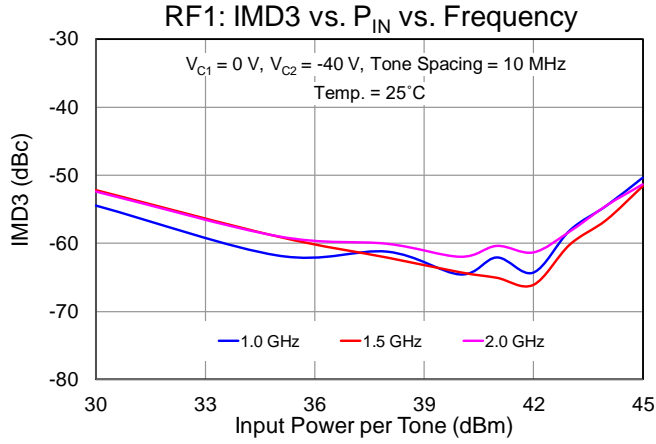
Performance Plots – Compression (CW)



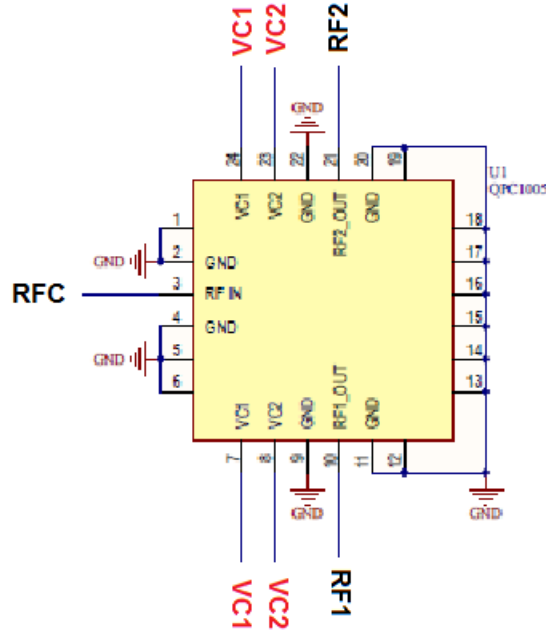
Performance Plots – Compression (CW)



Performance Plots – Linearity



Application Circuit



Notes:

1. This switch can be configured as a Single Pole, Single Throw (SPST) by terminating one unused RF switched port with a 50 Ohm load.
2. VC1 can be biased from either pin 7 or 24 and the non-biased pin can be left open.
3. VC2 can be biased from either pin 8 or 23 and the non-biased pin can be left open.
4. External components are not required

Bias Up Procedure

1. VC1 or VC2 set to 0 V (see Function Table for RF Path)
2. VC2 or VC1 set to -40 V (see Function Table for RF Path)
3. Apply RF signal to RF Input

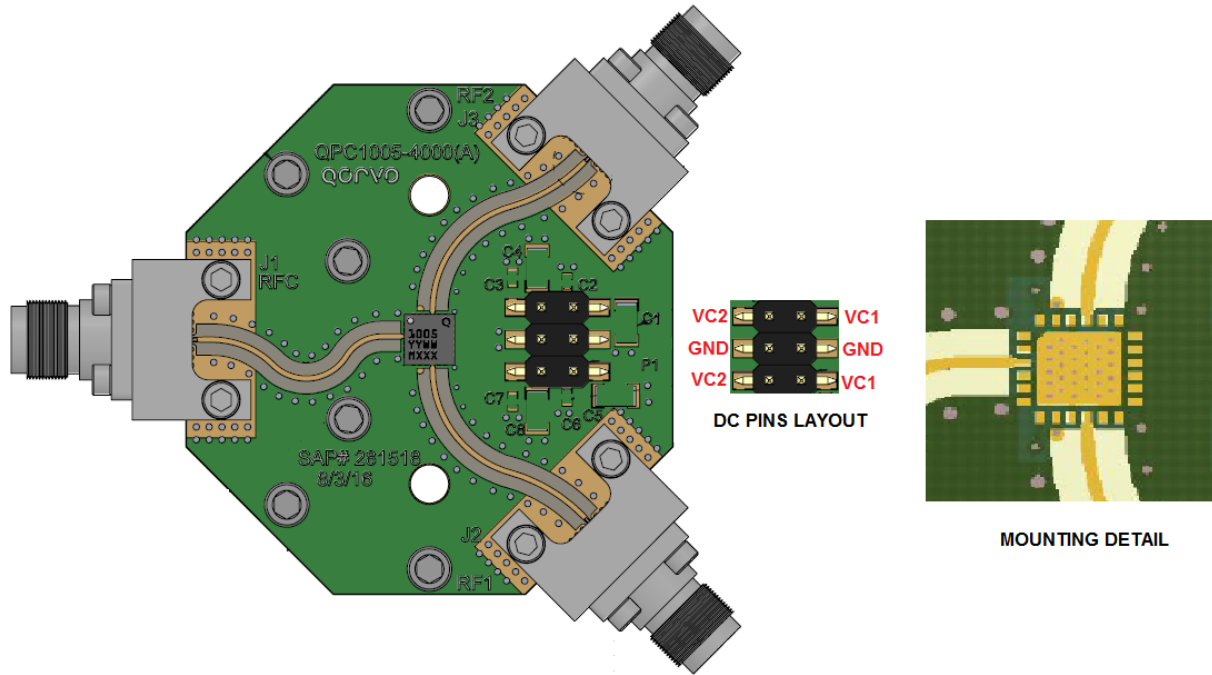
Bias Up Down

1. Turn off RF supply
2. Turn VC2 or VC1 to 0 V
3. Turn VC1 or VC2 to 0 V

Function Table

RF Path	State	VC1	VC2
RFC to RF1 ON	On-State (Insertion Loss)	0 V	-40 V
	Off-State (Isolation)	-40 V	0 V
RFC to RF2 ON	On-State (Insertion Loss)	-40 V	0 V
	Off-State (Isolation)	0 V	-40 V

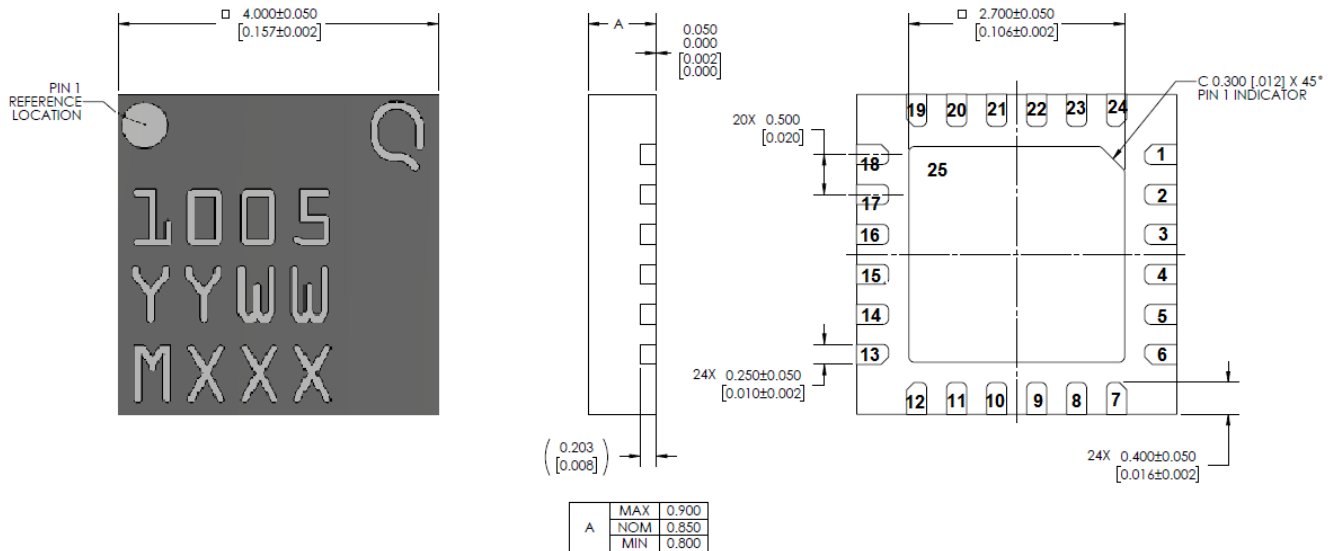
Evaluation Board (EVB) Assembly Layout.



Notes:

1. This switch can be configured as a Single Pole, Single Throw (SPST) by terminating one unused RF switched port with a 50 Ohm load.
2. V_{C1} can be biased from either pin and the non-biased pin can be left open.
3. V_{C2} can be biased from either pin and the non-biased pin can be left open.
4. External components are not required

Mechanical Information



Units: millimeters

Tolerances: unless specified

x.xx = ± 0.25

x.xxx = ± 0.100

Materials:

Base: Cu Alloy

Packaged Exposed Metallization is gold plated

Marking:

QPC1005: Part number

YY: Part Assembly year

WW: Part Assembly week

MXXX: Batch ID

Pin Description

Pad No.	Symbol	Description
1, 5, 6, 11-20,	N/C	Not connected internally. Recommended to be grounded at EVB level
2, 4, 9, 22	GND	Ground. Connected to GND paddle (pin 25); should be grounded on PCB to improve isolation
3	RFC	RF common port (port 1); matched to 50 Ω; DC coupled
7, 24	V _{C1}	Control voltage #1; External components are not required
8, 23	V _{C2}	Control voltage #2; External components are not required
10	RF1	RF switched port 2; matched to 50 Ω; DC coupled
21	RF2	RF switched port 3; matched to 50 Ω; DC coupled
25	GND	Backside Paddle. Multiple vias should be employed to minimize inductance and thermal resistance.

Solderability

1. Compatible with the latest version of J-STD-020, Lead-free solder, 260° C soldering process.
2. The use of no-clean solder to avoid washing after soldering is recommended.
3. Contact plating: Ni-Pd-Au.

Recommended Soldering Profile

